

Accession number:20123215326110

Title:Carrier density dependence of the nonlinear absorption of intense THz radiation in GaAs

Authors:Sharma, G. (1); Al-Naib, I. (1); Hafez, H. (1); Morandotti, R. (1); Cooke, D.G. (2); Ozaki, T. (1)

Author affiliation:(1) INRS-EMT, 1650 Boul. Lionel-Boulet, Varennes, QC J3X 1S2, Canada; (2) Department of Physics, McGill University, Montreal, QC H3A 2T8, Canada

Corresponding author:Sharma, G.

Source title:Optics Express

Abbreviated source title:Opt. Express

Volume:20

Issue:16

Issue date:July 30, 2012

Publication year:2012

Pages:18016-18024

Language:English

E-ISSN:10944087

Document type:Journal article (JA)

Publisher:Optical Society of America, 2010 Massachusetts Avenue NW, Washington, DC 20036-1023, United States

Abstract:We study the carrier density dependence of nonlinear terahertz (THz) absorption due to field-induced intervalley scattering in photoexcited GaAs using the optical-pump/THz-probe technique. The intervalley scattering in GaAs is strongly dependent on the photo-carrier density. As the carrier density is increased from $1 \times 10^{17}/\text{cm}^3$ to $4.7 \times 10^{17}/\text{cm}^3$, the nonlinear absorption bleaching increases. However, if the carrier density is increased further above $4.7 \times 10^{17}/\text{cm}^3$, the trend reverses and the bleaching is reduced. The initial increase in absorption bleaching is because, unlike low THz field, high THz field experiences intervalley scattering and nonparabolicity of the conduction band. On the other hand, a simple electron transport model shows that the reduction in intervalley scattering is mainly due to the increase in the electron-hole scattering rate with the increase in the carrier density. This increase in the electron-hole scattering rate limits the maximum kinetic energy attainable by the electrons and thus reduces the observed nonlinear absorption. © 2012 Optical Society of America.

Number of references:37

Main heading:Carrier concentration

Controlled terms:Electron scattering - Gallium arsenide - Semiconducting gallium

Uncontrolled terms:Absorption bleaching - Density dependence - Electron transport - Electron-hole scatterings - Field-induced - GaAs - Intervalley scattering - Non parabolicity - Nonlinear absorptions - Photocarrier - Terahertz - THz fields - THz radiation

Classification code:712.1.1 Single Element Semiconducting Materials - 804 Chemical Products Generally - 931.3 Atomic and Molecular Physics

DOI:10.1364/OE.20.018016

Database:Compendex

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